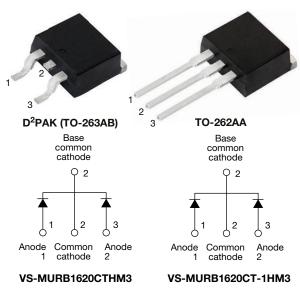
www.vishay.com

VS-MURB1620CTHM3, VS-MURB1620CT-1HM3

Vishay Semiconductors

Ultrafast Rectifier, 2 x 8 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 8 A							
V _R	200 V							
V _F at I _F	0.895 V							
t _{rr} (typ)	19 ns							
T _J max.	175 °C							
Package	D ² PAK (TO-263AB), TO-262AA							
Circuit configuration	Common cathode							

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Meets JESD 201 class 1 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

MECHANICAL DATA

Case: D²PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS									
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage		V _{RRM}		200	V				
Average rectified forward current	per leg			8.0					
	total device	I _{F(AV)}	Rated V _R , T _C = 150 °C	16	٨				
Non-repetitive peak surge current per leg		I _{FSM}		100	A				
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16					
Operating junction and storage temperatures		T _J , T _{Stg}		-65 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-				
Forward voltage	V _F	I _F = 8 A		-	0.975	V			
		I _F = 8 A, T _J = 150 °C	-	-	0.895				
Reverse leakage current		$V_{R} = V_{R}$ rated		-	5				
neverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA 250			
Junction capacitance	CT	V _R = 200 V	-	25	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

Revision: 07-Jun-2023

1

Document Number: 94852

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



COMPLIANT HALOGEN

FREE



VS-MURB1620CTHM3, VS-MURB1620CT-1HM3

www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 10$	I _F = 1.0 A, dI _F /dt = 100 A/µs, V _R = 30 V			-			
		T _J = 25 °C		-	20	-	ns		
		T _J = 125 °C	I _F = 8 A dI _F /dt = 200 A/µs	-	34	-			
Back receivery ourrent	I _{RRM}	T _J = 25 °C		-	1.7	-	A		
Peak recovery current		T _J = 125 °C	$V_{\rm B} = 160 \text{ V}$	-	4.2	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C	VR - 100 V	-	23	-	nC		
		T _J = 125 °C		-	75	-	no		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction to case per leg	R _{thJC}		-	-	3.0					
Thermal resistance, junction to ambient per leg			-	-	50	°C/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-					
Weight			-	2.0	-	g				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking davias		Case style D ² PAK (TO-263AB)	MURB1620CTH			•				
Marking device		Case style TO-262AA	MURB16	620CT-1H						

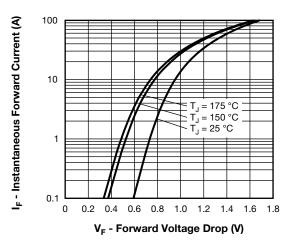


Fig. 1 - Typical Forward Voltage Drop Characteristics

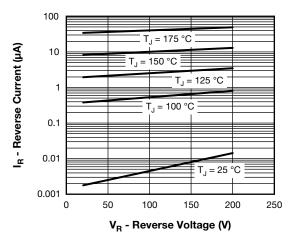


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

VISHAY. www.vishay.com

VS-MURB1620CTHM3, VS-MURB1620CT-1HM3

Vishay Semiconductors

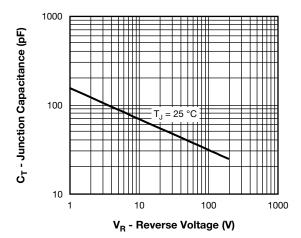


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

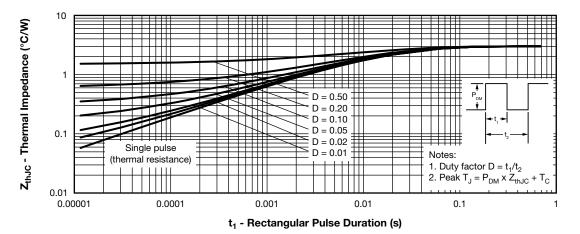
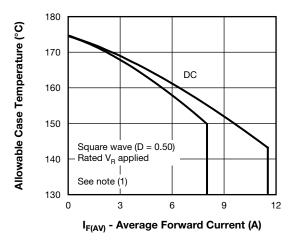


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

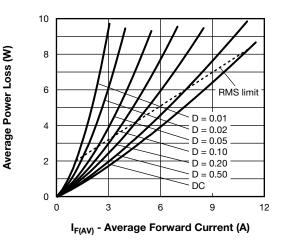




Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$





Revision: 07-Jun-2023

3

Document Number: 94852

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

VS-MURB1620CTHM3, VS-MURB1620CT-1HM3 ISHAY www.vishay.com **Vishay Semiconductors** 60 200 V_R = 160 V V_R = 160 V T_J = 125 °C T₁ = 125 °C $I_{\rm F} = 30 \, {\rm A}$ = 25 °C T_J = 25 °C 50 160 I_F = 15 A $I_{c} = 8 A$ I_F = 30 A $I_{F} = 15 A$ 1 40 120 Q_{rr} (nC) I_F = 8 A t_{rr} (ns) Ξ 30 80 20 40 10 0 100 1000 100 1000 dl_F/dt (A/µs) dl_F/dt (A/µs)

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt



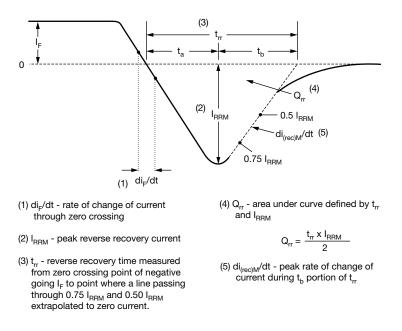


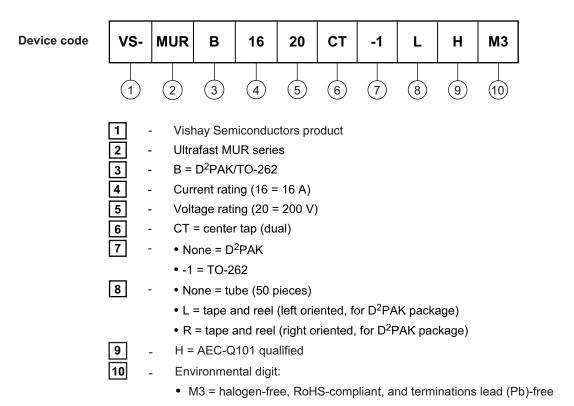
Fig. 9 - Reverse Recovery Waveform and Definitions

www.vishay.com

VS-MURB1620CTHM3, VS-MURB1620CT-1HM3

Vishay Semiconductors

ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-MURB1620CTHM3	50	Antistatic plastic tube							
VS-MURB1620CT-1HM3	50	Antistatic plastic tube							
VS-MURB1620CTLHM3	800	13" diameter reel							
VS-MURB1620CTRHM3	800	13" diameter reel							

LINKS TO RELATED DOCUMENTS								
Dimensions	TO-263AB (D ² PAK)	www.vishay.com/doc?95046						
	TO-262AA	www.vishay.com/doc?95419						
Part marking information	TO-263AB (D ² PAK)	www.vishay.com/doc?95444						
	TO-262AA	www.vishay.com/doc?95443						
Packaging information	TO-263AB (D ² PAK)	www.vishay.com/doc?95032						
SPICE model		www.vishay.com/doc?96995						

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

www.vishay.com

SHA



SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 08-Jul-15

1

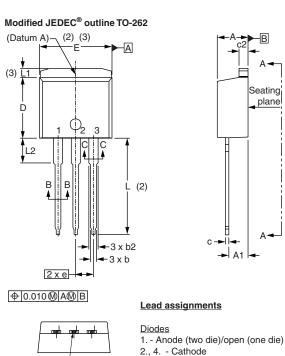
Outline Dimensions



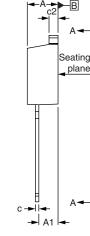
Vishay Semiconductors

TO-262

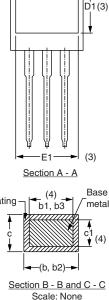
DIMENSIONS in millimeters and inches



Lead tip -



E1 Plating



Е

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. А 4.06 4.83 0.160 0.190 2.03 A1 3.02 0.080 0.119 b 0.51 0.99 0.020 0.039 b1 0.51 0.89 0.020 0.035 4 b2 1.14 1.78 0.045 0.070 1.14 1.73 0.045 0.068 4 b3 0.38 0.74 0.015 0.029 С 0.38 0.58 0.015 0.023 4 c1 1.14 1.65 0.045 0.065 c2 D 8.51 9.65 0.335 0.380 2 D1 6.86 8.00 0.270 0.315 3 Е 9.65 10.67 0.380 0.420 2, 3 E1 7.90 8.80 0.311 0.346 3 0.100 BSC 2.54 BSC е L 13.46 14.10 0.530 0.555 L1 _ 1.65 0.065 3 _ 3.36 0.132 0.146 L2 3.71

3. - Anode

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC TO-262 except A1 (maximum), (6) b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

Revision: 11-Jul-2019

Document Number: 95419

1 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2025 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2025

1